

# Photo-Responsive Molecular Junctions Activated by Perovskite/Graphene Heterostructure Electrode

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The original version of this Article contained errors.

First, Figures 4a and 4b are mistakenly switched. The correct Figure 4 is following.

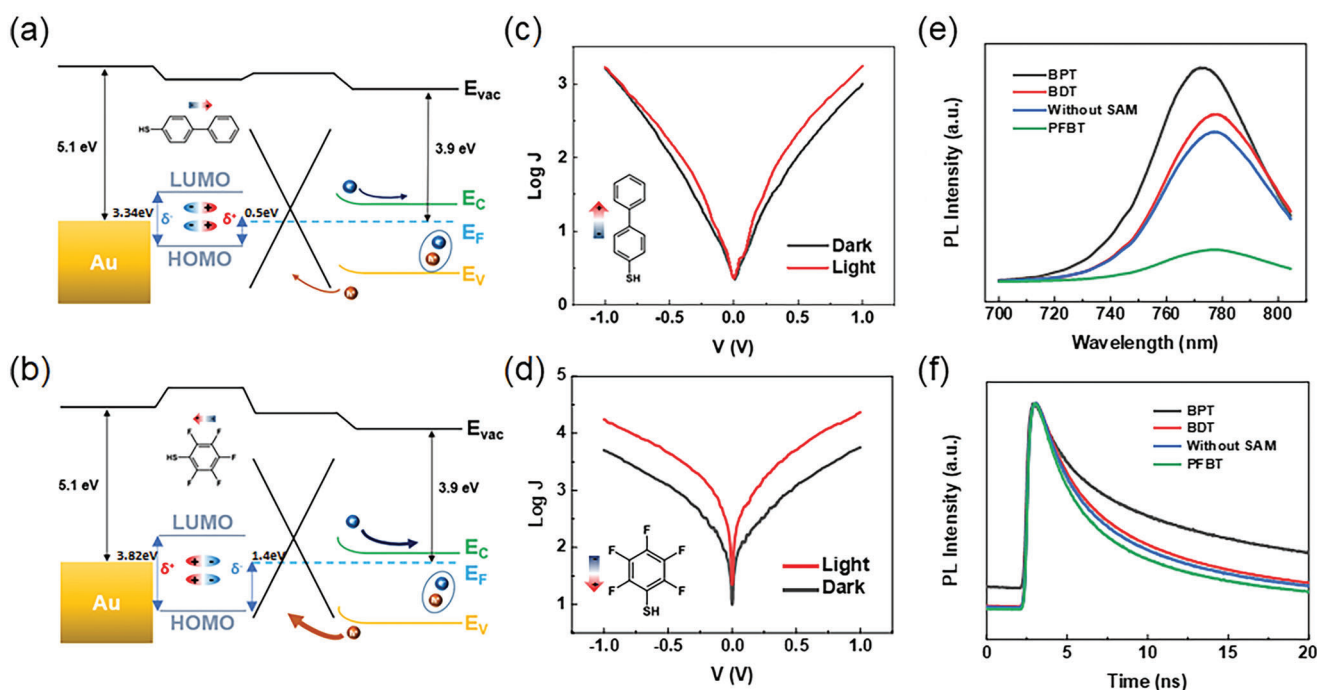


Figure 4.

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Table 1.

		$\Gamma_B$ (meV)	$\Gamma_T$ (meV)	$E_0$ (eV)	$\alpha$
<b>BPT</b>	Dark	44	23	0.50	0.43
	Light	44	34	0.48	0.445
<b>BDT</b>	Dark	49	21	0.52	0.44
	Light	49	30	0.49	0.48
<b>PFBT</b>	Dark	50	40	0.8	0.42
	Light	50	115	0.75	0.45

Second,  $\frac{2e}{h}$  is omitted from the equation (3) of the manuscript and the equation (S3) of the Supporting Information. So, the correct equations (3) and (S3) are following.

$$I(V) = \frac{2e}{h} \int_{-\infty}^{\infty} T(E, V) [f_B(E) - f_T(E + eV)] dE \quad (3)$$

$$I(V_{bias}) = \frac{2e}{h} \int_{-\infty}^{\infty} dET(E) (f(E, \mu) - f(E, \mu + eV_{bias})) \quad (S3)$$

Third, the  $E_0$  value of the BPT(biphenyl-4-thiol) molecule given in Table 1 and in the text of the manuscript are not consistent by a mistake. Correct Table 1 is following.

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